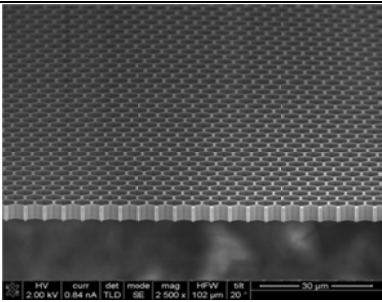
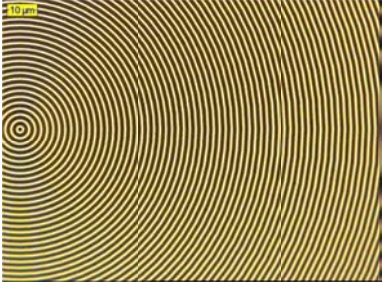


Replication

Etching: DRIE and RIE

MiPlaza Philips Research Europe, The Netherlands



Contact:	Dr. Eric van den Heuvel Email eric.van.den.heuvel@philips.com • Phone + 31(40)2742163						
Material class:	Silicon X	Polymer X	Metal X	Ceramic X	Glass	Organic	Other
Short technology description:	<p>Reactive ion etching is a combination of physical and chemical etching and is used for making high-resolution and/or high aspect ratio structures. We offer etching of metals (Al, Cr, Ti, W(Ti)), dielectrics (SiO₂, SiN) and Si.</p> <p>Deep Reactive Ion Etching is the pattern transfer method for making high-aspect ratio trenches and vias. DRIE of Si is well known in Si-based MEMS processing, achieving etching depths of more than 100 µm, and even through-wafer processing is feasible.</p> <p>The installation on offer has been updated to a STS CPX cluster tool with APS etching chamber.</p> <p>Further, deep etching of silicon oxide can be very interesting for making micro-fluidic channels. Our capability is limited to depths of approximately 20 µm.</p>						
Typical structures and designs: Depending on - material - mask - RIE chemistry	 						
Special features:	– Deep Si and SiO ₂ etch						
Limitations, constraints:	– Limited range of materials, mask to be chosen carefully						
Material examples:							